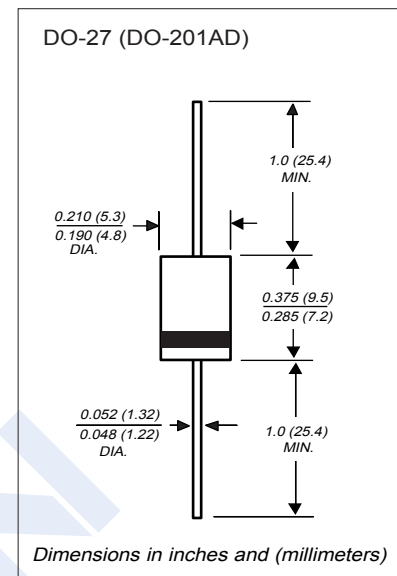


## Schottky Diodes

### SB320 ~ SB3200

#### ■ Features

- Metal-Semiconductor junction with guard ring
- Epitaxial construction
- Low forward voltage drop
- High current capability
- The plastic material carries UL recognition 94V-0



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	SB 320	SB 330	SB 340	SB 350	SB 360	SB 380	SB 3100	SB 3150	SB 3200	Unit	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	20	30	40	50	60	80	100	150	200	V	
RMS Voltage	V <sub>RMS</sub>	14	21	28	35	42	56	70	105	140		
Maximum DC Blocking Voltage	V <sub>DC</sub>	20	30	40	50	60	80	100	150	200		
Forward Voltage @ 3A	V <sub>F</sub>	0.55		0.7		0.85		0.87		0.9		
Averaged Forward Current	I <sub>FAV</sub>	3										A
Peak Forward Surge Current @ 8.3ms	I <sub>FSM</sub>	80										
Maximum DC Reverse Current Ta=25°C	I <sub>R</sub>	0.5					0.2					mA
Ta=100°C		10					5					
Typical Junction Capacitance	C <sub>j</sub>	180		150		110		100		80	pF	
Thermal Resistance.Junction- to-Ambient	R <sub>thJA</sub>	60										°C/W
Thermal Resistance.Junction- to-Case	R <sub>thJC</sub>	15										
Junction Temperature	T <sub>j</sub>	125										°C
Storage Temperature	T <sub>stg</sub>	-55 to 150										

# Schottky Diodes SB320 ~ SB3200

## ■ Typical Characteristics

FIG. 1-TYPICAL FORWARD CURRENT DERATING CURVE

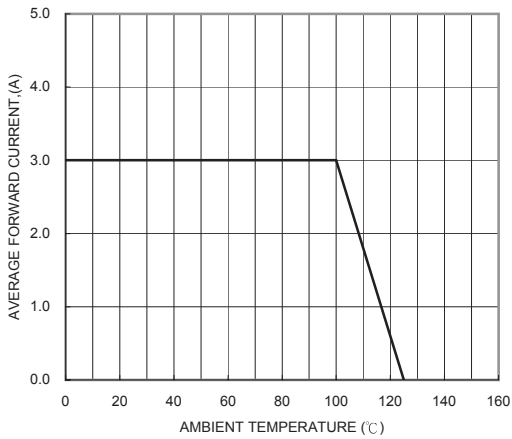


FIG. 2-TYPICAL FORWARD CHARACTERISTICS

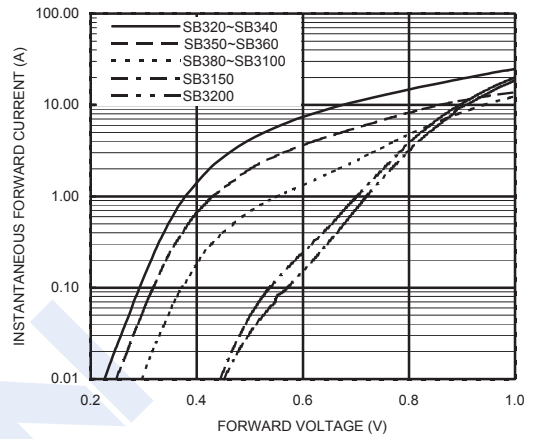


FIG. 3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

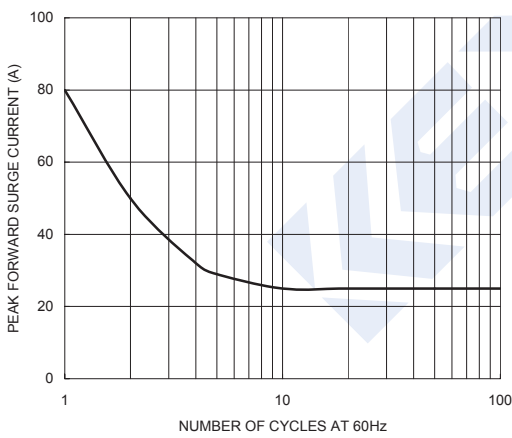


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

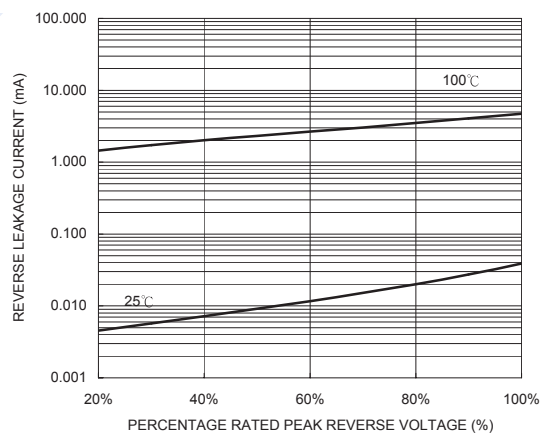


FIG. 5-TYPICAL JUNCTION CAPACITANCE

